

10/764,273

(FILE 'HOME' ENTERED AT 20:36:54 ON 11 DEC 2005)

FILE 'CAPLUS' ENTERED AT 20:37:08 ON 11 DEC 2005

=> s CVD and solvent

64240 CVD

648169 SOLVENT

L1 462 CVD AND SOLVENT

=> s l2 and metal amide

L2 NOT FOUND

The L-number entered could not be found. To see the definition of L-numbers, enter DISPLAY HISTORY at an arrow prompt (=>).

=> s l1 and metal amide

1613505 METAL

121939 AMIDE

489 METAL AMIDE

(METAL(W)AMIDE)

L2 1 L1 AND METAL AMIDE

=> d bib abs

L2 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2000:790762 CAPLUS

DN 133:342806

TI Liquid precursors for CVD formation of alkali metal compounds such as oxides

IN Gordon, Roy G.; Broomhall-dillard, Randy N. R.

PA President and Fellows of Harvard College, USA

SO PCT Int. Appl., 28 pp.

CODEN: PIXXD2

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	WO 2000067300	A1	20001109	WO 2000-US11415	20000428
	W: CA, JP, KR, US				
	RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				

PRAI US 1999-131527P A2 19990429

AB Volatile liquid precursors are provided for the formation of alkali metal-containing materials. The liquid precursors comprise alkali metal amides. For example, a volatile liquid compound was formed by reacting Bu Li with bis(ethyldimethylsilyl)amine. Films containing alkali metals are deposited from vapors of the precursor liqs. and, optionally, O or other sources of O. This process may be used to deposit Li niobate films having nonlinear optical properties. The liquid precursors may also be used for spray coating, spin coating and sol-gel deposition of materials containing alkali metals.

RE.CNT 7 THERE ARE 7 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> s liquid precursors and CVD

706242 LIQUID

112306 PRECURSORS

82 LIQUID PRECURSORS

(LIQUID(W)PRECURSORS)

64240 CVD

L3 29 LIQUID PRECURSORS AND CVD

=> s l3 and solvent

648169 SOLVENT

L4 2 L3 AND SOLVENT

=> d 1-2 bib abs

L4 ANSWER 1 OF 2 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2000:878087 CAPLUS
 DN 134:93473
 TI MOCVD of high-k dielectrics, tantalum nitride and copper from directly
 injected **liquid precursors**
 AU Senzaki, Yoshihide; Hochberg, Arthur K.; Norman, John A. T.
 CS Schumacher, Carlsbad, CA, 92009, USA
 SO Advanced Materials for Optics and Electronics (2000), 10(3-5), 93-103
 CODEN: AMELE7; ISSN: 1057-9257
 PB John Wiley & Sons Ltd.
 DT Journal; General Review
 LA English
 AB A review, with 67 refs.,. Thin films of Ta oxide and Ta nitride for
 microelectronics applications can be deposited by MOCVD using direct
 injection of same liquid precursors R-N = Ta(NEt₂)₃. High-k mixed-metal
 oxides, such as Zr-Sn-Ti-O, metal doped TaOx and Zr silicate, can also be
 deposited at relatively low temps. from liquid mixts. as single-source
 precursors without **solvent**. This solventless **CVD**
 system is considered a more cost effective and environmentally benign
 process than conventional liquid injection of metal-organic precursors
 dissolved in organic solvents. In addition, recent advances in Cu **CVD**
 precursors are reviewed.
 RE.CNT 67 THERE ARE 67 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L4 ANSWER 2 OF 2 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2000:790762 CAPLUS
 DN 133:342806
 TI **Liquid precursors** for **CVD** formation of
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 IN Gordon, Roy G.; Broomhall-dillard, Randy N. R.
 PA President and Fellows of Harvard College, USA
 SO PCT Int. Appl., 28 pp.
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